

Wantae Lim

List of Publications by Year in descending order

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33
papers

1,557
citations

361413

20
h-index

414414

32
g-index

33
all docs

33
docs citations

33
times ranked

1789
citing authors

#	ARTICLE	IF	CITATIONS
1	Recent advances in wide bandgap semiconductor biological and gas sensors. Progress in Materials Science, 2010, 55, 1-59.	32.8	247
2	Room temperature deposited indium zinc oxide thin film transistors. Applied Physics Letters, 2007, 90, 232103.	3.3	132
3	Effects of ambient atmosphere on the transfer characteristics and gate-bias stress stability of amorphous indium-gallium-zinc oxide thin-film transistors. Applied Physics Letters, 2010, 96, .	3.3	121
4	High performance indium gallium zinc oxide thin film transistors fabricated on polyethylene terephthalate substrates. Applied Physics Letters, 2008, 93, .	3.3	107
5	High-Performance Indium Gallium Zinc Oxide Transparent Thin-Film Transistors Fabricated by Radio-Frequency Sputtering. Journal of the Electrochemical Society, 2008, 155, H383.	2.9	94
6	Room temperature hydrogen detection using Pd-coated GaN nanowires. Applied Physics Letters, 2008, 93, .	3.3	91
7	High mobility InGaZnO ₄ thin-film transistors on paper. Applied Physics Letters, 2009, 94, .	3.3	87
8	Hydrogen sensing with Pt-functionalized GaN nanowires. Sensors and Actuators B: Chemical, 2009, 140, 196-199.	7.8	82
9	Low-voltage indium gallium zinc oxide thin film transistors on paper substrates. Applied Physics Letters, 2010, 96, .	3.3	74
10	Stable room temperature deposited amorphous InGaZnO ₄ thin film transistors. Journal of Vacuum Science & Technology B, 2008, 26, 959.	1.3	66
11	Temperature dependence of current-voltage characteristics of Ni ²⁺ /AlGaIn/GaN Schottky diodes. Applied Physics Letters, 2010, 97, .	3.3	49
12	Growth and Characterization of GaN Nanowires for Hydrogen Sensors. Journal of Electronic Materials, 2009, 38, 490-494.	2.2	42
13	Low-temperature-fabricated InGaZnO ₄ thin film transistors on polyimide clean-room tape. Applied Physics Letters, 2008, 93, .	3.3	41
14	Selective-hydrogen sensing at room temperature with Pt-coated InN nanobelts. Applied Physics Letters, 2008, 93, .	3.3	35
15	Indium zinc oxide thin films deposited by sputtering at room temperature. Applied Surface Science, 2008, 254, 2878-2881.	6.1	32
16	RF Characteristics of Room-Temperature-Deposited, Small Gate Dimension Indium Zinc Oxide TFTs. Electrochemical and Solid-State Letters, 2008, 11, H60.	2.2	32
17	Improvement in bias stability of amorphous-InGaZnO ₄ thin film transistors with SiO _x passivation layers. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, 116-119.	1.2	32
18	Highly sensitive AlGaIn/GaN diode-based hydrogen sensors using platinum nanonetworks. Sensors and Actuators B: Chemical, 2012, 164, 64-68.	7.8	32

#	ARTICLE	IF	CITATIONS
19	Carrier concentration dependence of Ti ⁺ Au specific contact resistance on n-type amorphous indium zinc oxide thin films. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	31
20	Light-Emitting Diodes with Hierarchical and Multifunctional Surface Structures for High Light Extraction and an Antifouling Effect. <i>Small</i> , 2016, 12, 161-168.	10.0	22
21	Hydrogen sensing characteristics of non-polar a-plane GaN Schottky diodes. <i>Current Applied Physics</i> , 2010, 10, 1029-1032.	2.4	20
22	Metastable centers in AlGaN/AlN/GaN heterostructures. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012, 30, .	1.2	14
23	Titanium oxide nanotube arrays for high light extraction efficiency of GaN-based vertical light-emitting diodes. <i>Nanoscale</i> , 2016, 8, 10138-10144.	5.6	12
24	Room-Temperature-Deposited Indium-Zinc Oxide Thin Films with Controlled Conductivity. <i>Electrochemical and Solid-State Letters</i> , 2007, 10, H267.	2.2	11
25	Enhanced optical output power of InGaN/GaN vertical light-emitting diodes by ZnO nanorods on plasma-treated N-face GaN. <i>Nanoscale</i> , 2014, 6, 10187-10192.	5.6	11
26	SiO ₂ nanohole arrays with high aspect ratio for InGaN/GaN nanorod-based phosphor-free white light-emitting-diodes. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, 042204.	1.2	10
27	Oxygen gas sensing at low temperature using indium zinc oxide-gated AlGaN/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, 376-379.	1.2	9
28	Light extraction efficiency of GaN-based LEDs with non-periodic and periodic sub-wavelength structures. <i>Journal of the Korean Physical Society</i> , 2013, 62, 770-774.	0.7	7
29	Fabrication of compositional graded Si _{1-x} Gex layers by using thermal oxidation. <i>Applied Physics Letters</i> , 2009, 94, 202104.	3.3	6
30	Effect of oxygen plasma treatment on nonalloyed Al/Ti-based contact for high power InGaN/GaN vertical light-emitting diodes. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, 010602.	1.2	5
31	Light-Emitting Diodes: Light-Emitting Diodes with Hierarchical and Multifunctional Surface Structures for High Light Extraction and an Antifouling Effect (<i>Small</i> 2/2016). <i>Small</i> , 2016, 12, 138-138.	10.0	2
32	Recent Advances in Wide Bandgap Semiconductor Biological and Gas Sensors. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1202, 138.	0.1	1
33	High Temperature Stable Contacts for GaN HEMTs and LEDs. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1108, 1.	0.1	0